# **PUB4314** (PU4314)

## Silicon NPN/PNP planar type

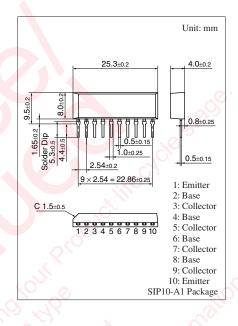
### For low-voltage switching

#### ■ Features

- ullet Low collector-emitter saturation voltage  $V_{\text{CE(sat)}}$
- Satisfactory linearity of forward current transfer ratio h<sub>FE</sub>
- High-speed switching
- NPN 2 elements + PNP 2 elements

## ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	±40	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	±20	V	
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	±5	V	
Collector current	$I_{C}$	±7	A	
Peak collector current	I <sub>CP</sub>	±12	A	
Collector power dissipation	P <sub>C</sub>	15	W	
$T_a = 25^{\circ}C$		3.5		
Junction temperature	T <sub>j</sub>	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	

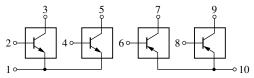


## ■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base	open)	V <sub>CEO</sub>	$I_{\rm C} = \pm 10 \text{ mA}, I_{\rm B} = 0$	±20	10	10	V
Collector-base cutoff current (Emitte	r open)	$I_{CBO}$	$V_{CB} = \pm 40 \text{ V}, I_{E} = 0$	7) /		±50	μΑ
Emitter-base cutoff current (Collecto	r open)	I <sub>EBO</sub>	$V_{EB} = \pm 5 \text{ V}, I_C = 0$	70		±50	μΑ
Forward current transfer ratio		h <sub>FE1</sub>	$V_{CE} = \pm 2 \text{ V}, I_{C} = \pm 0.1 \text{ A}$	45	0		_
		h <sub>FE2</sub>	$V_{CE} = \pm 2 \text{ V}, I_{C} = \pm 2 \text{ A}$	60		260	
Collector-emitter saturation vol	tage	V <sub>CE(sat)</sub>	$I_C = \pm 5 \text{ A}, I_B = \pm 0.16 \text{ A}$	0		±0.6	V
Base-emitter saturation voltage	3	V <sub>BE(sat)</sub>	$I_C = \pm 5 \text{ A}, I_B = \pm 0.16 \text{ A}$	)		±1.5	V
Transition frequency		$f_T$	$V_{CE} = \pm 10 \text{ V}, I_{C} = \pm 0.5 \text{ A}, f = 10 \text{ MHz}$		150		MHz
Turn-on time	NPN	t <sub>on</sub>	$I_C = \pm 2 A$		0.3		μs
	PNP		$I_{B1} = \pm 66 \text{ mA}, I_{B2} = \pm 66 \text{ mA}$		0.1		
Storage time	NPN	t <sub>stg</sub>	$V_{CC} = \pm 20 \text{ V}$		0.3		μs
	PNP		113		0.5		
Fall time	NPN	$t_{\mathrm{f}}$	S		0.1		μs
	PNP	.0			0.1		

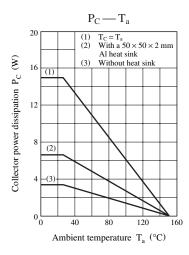
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

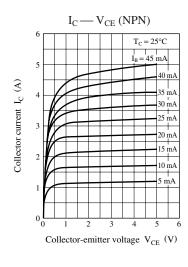
### ■ Internal Connection

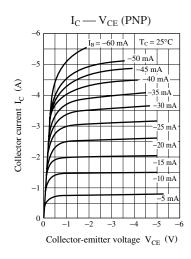


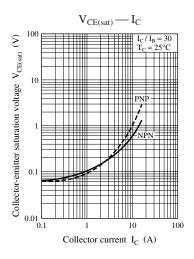
Note) The part number in the parenthesis shows conventional part number.

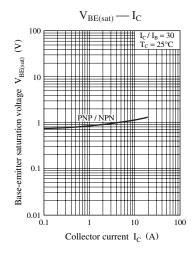
PUB4314 Panasonic

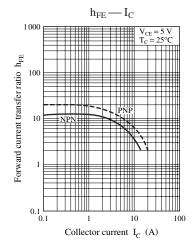


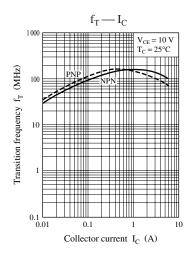


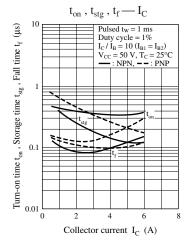


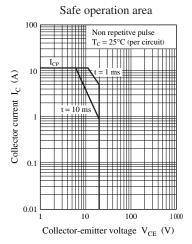












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